



175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	I _D Τ _C = +25°C
40\/	15mΩ @ $V_{GS} = -10V$	-55A
-40V	23mΩ @ $V_{GS} = -4.5V$	-50A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Reverse Polarity Protection
- Motor Control
- Power Management

Features and Benefits

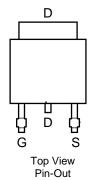
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMPH4013SK3Q)

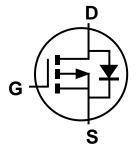
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View





Equivalent Circuit

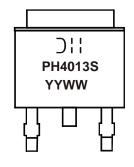
Ordering Information (Note 4)

-			
	Part Number	Case	Packaging
	DMPH4013SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information





Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-40	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	l _D	-55 -40	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	-120	Α		
Maximum Body Diode Forward Current (Note 6)			Is	-3.6	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	-120	Α
Avalanche Current, L = 0.1mH (Note 7)			I _{AS}	-40	Α
Avalanche Energy, L = 0.1mH (Note 7)			E _{AS}	69	mJ

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{ heta JA}$	71	°C/W
Total Power Dissipation (Note 6)		P_{D}	3.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{ heta JA}$	41	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.7	C/VV
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	В		10	15	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}		15	23	1115.2	$V_{GS} = -4.5V, I_D = -8A$	
Diode Forward Voltage	V_{SD}		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		4004	_		$V_{DS} = -20V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		309	_	pF		
Reverse Transfer Capacitance	Crss		229	_			
Gate Resistance	R_g		3.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_{g}		31	_			
Total Gate Charge (V _{GS} = -10V)	Q_g		67	_	nC	$V_{DS} = -20V, I_{D} = -10A$	
Gate-Source Charge	Q_{gs}		13.2	_	IIC		
Gate-Drain Charge	Q_{gd}		11	_			
Turn-On Delay Time	t _{D(ON)}		9.9	_			
Turn-On Rise Time	t_R		32	_	200	$V_{GS} = -10V, V_{DD} = -20V,$	
Turn-Off Delay Time	t _{D(OFF)}		46	_	ns	$R_G = 3\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F		53	_			
Reverse Recovery Time	t _{RR}		19.5	_	ns	$I_F = -10A$, $di/dt = -100A/\mu s$	
Reverse Recovery Charge	Q_{RR}		11.6	_	nC	$I_F = -10A$, $di/dt = -100A/\mu s$	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

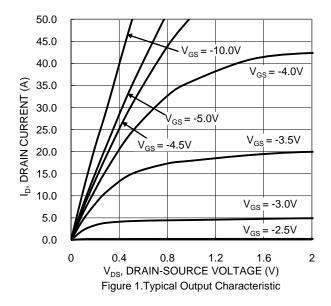
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





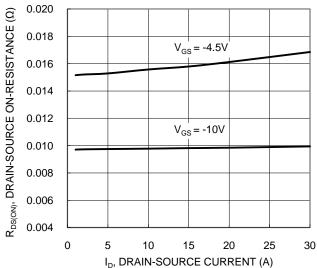


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

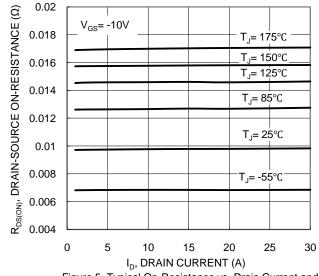


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

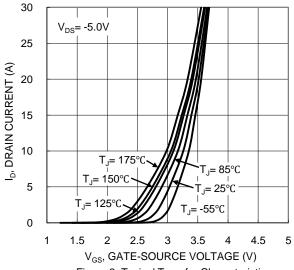


Figure 2. Typical Transfer Characteristic

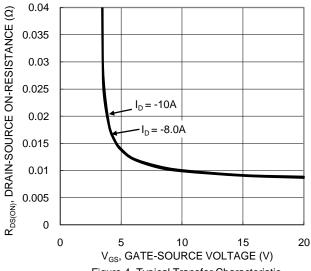


Figure 4. Typical Transfer Characteristic

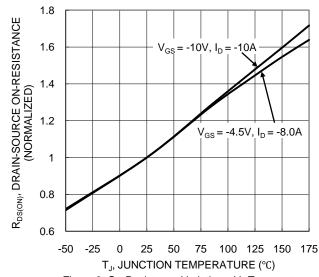


Figure 6. On-Resistance Variation with Temperature





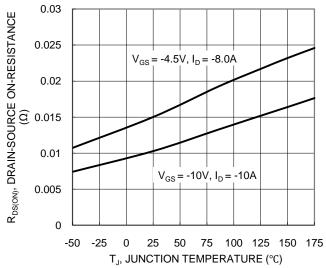
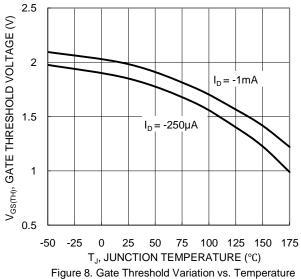
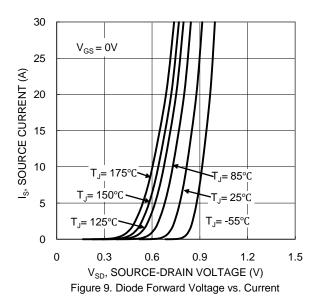
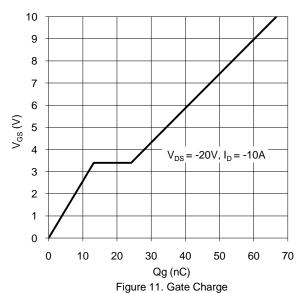
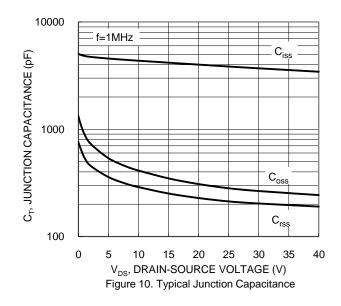


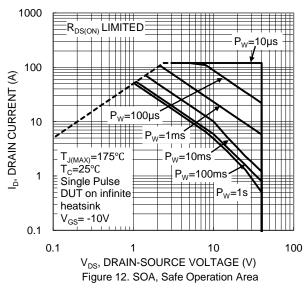
Figure 7. On-Resistance Variation with Temperature











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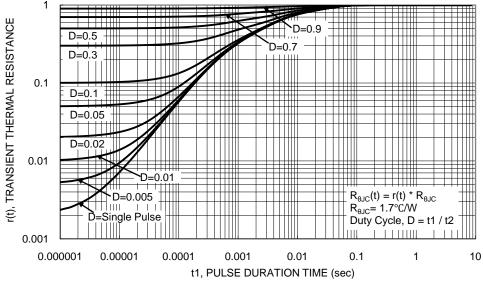


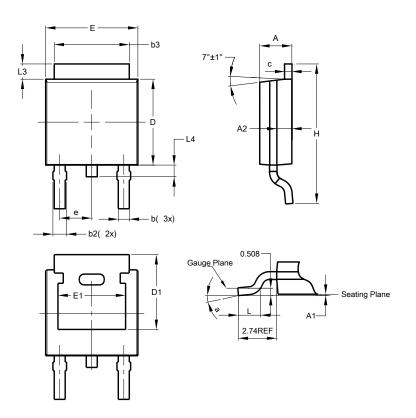
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

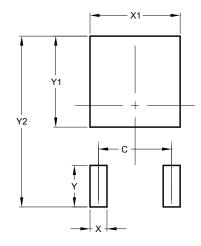


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
П	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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